CMPD6001
CMPD6001A
CMPD6001C
CMPD6001S

SURFACE MOUNT
LOW LEAKAGE
SILICON SWITCHING DIODE

EED
ENERGY EFFICIENT DEVICE
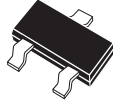
SOT-23 CASE

Central™
Semiconductor Corp.

DESCRIPTION:
The CENTRAL SEMICONDUCTOR CMPD6001 series types are silicon switching diodes manufactured by the epitaxial planar process, designed for switching applications requiring a extremely low leakage diode.

The following configurations are available:

CMPD6001	SINGLE	**MARKING CODE: ULO**
CMPD6001A	DUAL, COMMON ANODE	**MARKING CODE: ULA**
CMPD6001C	DUAL, COMMON CATHODE	**MARKING CODE: ULC**
CMPD6001S	DUAL, IN SERIES	**MARKING CODE: ULS**

MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	250	mA
Forward Surge Current, tp=1 μsec.	I_{FSM}	4000	mA
Forward Surge Current, tp=1 sec.	I_{FSM}	1000	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	V_R=75V		500	pA
V_{BR}	I_R=100μA	100		V
V_F	I_F=1.0mA		0.85	V
V_F	I_F=10mA		0.95	V
V_F	I_F=100mA		1.1	V
C_T	V_R=0, f=1.0 MHz		2.0	pF
t_{rr}	I_R=I_F=10mA, R_L=100Ω, Rec. to 1.0mA		3.0	μs

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SURFACE MOUNT
LOW LEAKAGE
SILICON SWITCHING DIODE

SOT-23 CASE - MECHANICAL OUTLINE
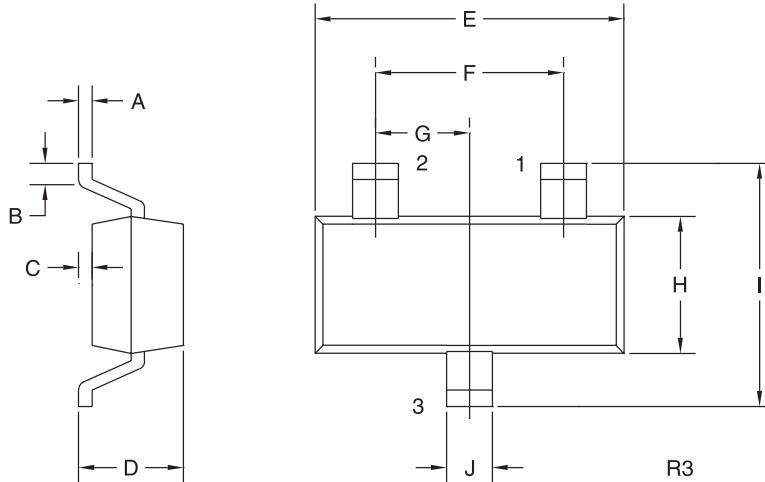
DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

Pin Configuration
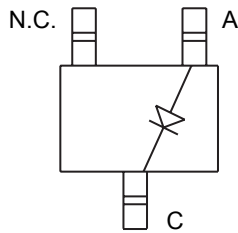
CMPD6001
MARKING
CODE: ULO
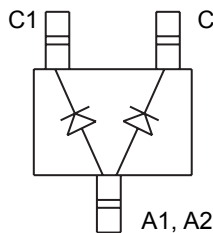
CMPD6001A
MARKING
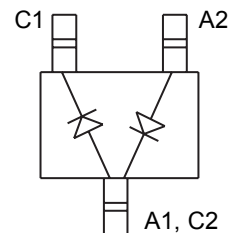**CODE: ULA**
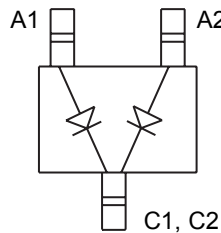
CMPD6001C
MARKING
CODE: ULC

CMPD6001S
MARKING
CODE: ULS

R2 (13-November 2002)